

Amendments to the Claims

This listing of claims replaces all prior versions and listings of claims in the application.

Listing of Claims

1-15. (Canceled)

16. (Currently Amended) ~~An active-matrix~~ A circuit comprising:

a transistor comprising a plurality of semiconductor islands;

~~a semiconductor layer;~~

a p-type impurity region provided in said semiconductor layer each of said semiconductor islands;

a first interlayer insulating film comprising silicon nitride provided over said semiconductor layer semiconductor islands;

a conductive layer comprising titanium and aluminum over said first interlayer insulating film; and

a second interlayer insulating film provided over said conductive layer to provide a leveled upper surface over said semiconductor layer islands,

~~wherein said titanium and said aluminum are formed in a multi-layer film~~

wherein each of said semiconductor islands has a planar area of $1000\ \mu\text{m}^2$ or less.

17. (Currently Amended) A circuit according to claim 16 wherein said ~~active-matrix~~ circuit is incorporated into a liquid-crystal display.

18. (Currently Amended) A circuit according to claim 16 wherein said ~~active-matrix~~ circuit is incorporated into an image sensor.

19. (Currently Amended) A circuit according to claim 16 wherein said ~~active-matrix~~ circuit is incorporated into a liquid-crystal electro-optical device.

20. (Currently Amended) A circuit according to claim 16 wherein ~~said semiconductor layer~~ each of said semiconductor islands comprises a crystal silicon.

21. (Currently Amended) An active matrix circuit comprising:
a transistor comprising a plurality of semiconductor islands and provided in a pixel;
~~a semiconductor layer;~~
a p-type impurity region provided in ~~said semiconductor layer~~ each of said semiconductor islands;
a first interlayer insulating film comprising a silicon nitride layer and a silicon oxide layer, said first interlayer insulating film provided over said semiconductor ~~layer~~ islands;
a conductive layer comprising titanium and aluminum over said first interlayer insulating film; ~~and~~
a second interlayer insulating film provided over said conductive layer to provide a leveled upper surface over said semiconductor ~~layer~~ islands; and
a pixel electrode provided over said second interlayer insulating film and connected with said p-type impurity region,
wherein each of said semiconductor islands has a planar area of $1000\ \mu\text{m}^2$ or less.

22. (Previously Presented): A circuit according to claim 21 wherein said active matrix circuit is incorporated into a liquid-crystal display.

23. (Previously Presented): A circuit according to claim 21 wherein said active matrix circuit is incorporated into an image sensor.

24. (Previously Presented): A circuit according to claim 21 wherein said active matrix circuit is incorporated into a liquid-crystal electro-optical device.

25. (Currently Amended) A circuit according to claim 21 wherein ~~said semiconductor layer~~ each of said semiconductor islands comprises a crystal silicon.

26. (Currently Amended) ~~An active matrix~~ A drive circuit comprising:
at least one transistor comprising a plurality of semiconductor islands;
~~a semiconductor layer;~~
a p-type impurity region provided in ~~said semiconductor layer~~ each of said semiconductor islands;
a first interlayer insulating film comprising silicon nitride provided over said semiconductor ~~layer~~ islands;
a conductive layer comprising titanium and aluminum over said first interlayer insulating film; and
a second interlayer insulating film provided over said conductive layer to provide a leveled upper surface over said semiconductor ~~layer~~ islands, and
wherein each of said semiconductor islands has a planar area of 1000 μm^2 or less.

27. (Previously Presented): A circuit according to claim 26 wherein said conductive layer comprises an electrode.

28. (Previously Presented): A circuit according to claim 26 wherein said conductive layer comprises a wiring.

29. (Currently Amended) A circuit according to claim 26 wherein said ~~active matrix~~ drive circuit is incorporated into a liquid-crystal display.

30. (Currently Amended) A circuit according to claim 26 wherein said ~~active matrix~~ drive circuit is incorporated into an image sensor.

31. (Currently Amended) A circuit according to claim 26 wherein said ~~active-matrix~~ drive circuit is incorporated into a liquid-crystal electro-optical device.

32. (Currently Amended) A circuit according to claim 26 wherein said ~~semiconductor~~ layer each of said semiconductor islands comprises a crystal silicon.

33. (Canceled).

34. (Currently Amended) ~~An active-matrix~~ A circuit comprising:
a transistor comprising a plurality of semiconductor islands;
~~a semiconductor layer;~~
a p-type impurity region provided in said ~~semiconductor layer~~ each of said semiconductor islands;
a first interlayer insulating film comprising silicon nitride provided over said semiconductor ~~layer~~ islands;
a conductive layer comprising titanium and aluminum over said first interlayer insulating film, said conductive layer connected with said p-type impurity region; and
a second interlayer insulating film provided over said conductive layer to provide a leveled upper surface over said semiconductor ~~layer~~ islands,
~~wherein said titanium and said aluminum are formed in a multi layer film.~~
wherein each of said semiconductor islands has a planar area of 1000 μm^2 or less.

35. (Currently Amended) A circuit according to claim 34 wherein said ~~active-matrix~~ circuit is incorporated into a liquid-crystal display.

36. (Currently Amended) A circuit according to claim 34 wherein said ~~active-matrix~~ circuit is incorporated into an image sensor.

37. (Currently Amended) A circuit according to claim 34 wherein ~~said semiconductor layer~~ each of said semiconductor islands comprises a crystal silicon.

38. (Currently Amended) An active matrix circuit comprising:
a transistor comprising a plurality of semiconductor islands;
~~a semiconductor layer;~~
a pair of p-type impurity region regions provided in said semiconductor layer each of said semiconductor islands;
a first interlayer insulating film comprising a silicon nitride layer and a silicon oxide layer, said first interlayer insulating film provided over said semiconductor ~~layer~~ islands;
a conductive layer comprising titanium and aluminum over said first interlayer insulating film, said conductive layer connected with one of said p-type impurity ~~region~~ regions; and
a second interlayer insulating film provided over said conductive layer to provide a leveled upper surface over said semiconductor ~~layer~~ islands; and
a pixel electrode provided over said second interlayer insulating film and connected with the other of said p-type impurity regions,
wherein each of said semiconductor islands has a planar area of 1000 μm^2 or less.

39. (Previously Presented) A circuit according to claim 38 wherein said active matrix circuit is incorporated into a liquid-crystal display.

40. (Previously Presented) A circuit according to claim 38 wherein said active matrix circuit is incorporated into an image sensor.

41. (Currently Amended) A circuit according to claim 38 wherein ~~said semiconductor layer~~ each of said semiconductor islands comprises a crystal silicon.

42. (Currently Amended) ~~An active matrix~~ A drive circuit comprising:

at least one transistor comprising a plurality of semiconductor islands;

~~a semiconductor layer;~~

a p-type impurity region provided in ~~said semiconductor layer~~ each of said semiconductor islands;

a first interlayer insulating film comprising silicon nitride provided over said semiconductor ~~layer~~ islands;

a conductive layer comprising titanium and aluminum over said first interlayer insulating film, said conductive layer connected with said p-type impurity region; and

a second interlayer insulating film provided over said conductive layer to provide a leveled upper surface over said semiconductor ~~layer~~ islands,

wherein each of said semiconductor islands has a planar area of $1000\ \mu\text{m}^2$ or less.

43. (Currently Amended) A circuit according to claim 42 wherein said ~~active-matrix~~ drive circuit is incorporated into a liquid-crystal display.

44. (Currently Amended) A circuit according to claim 42 wherein said ~~active-matrix~~ drive circuit is incorporated into an image sensor.

45. (Currently Amended) A circuit according to claim 42 wherein ~~said semiconductor layer~~ each of said semiconductor islands comprises a crystal silicon.